

Supplementary Materials: Realizing Efficient Photoelectrochemical Performance for Well-Designed CdS@ZnIn₂S₄ Heterostructure Photoanode with Directional Interfacial Charge Transfer Dynamics

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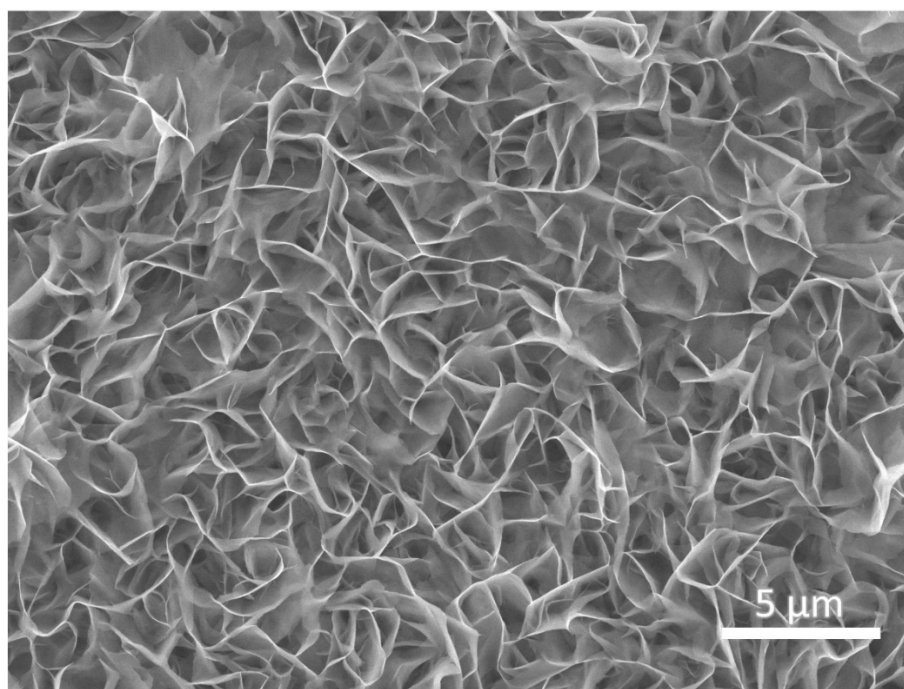


Figure S1. The FESEM images of CdS@ZIS (HC).

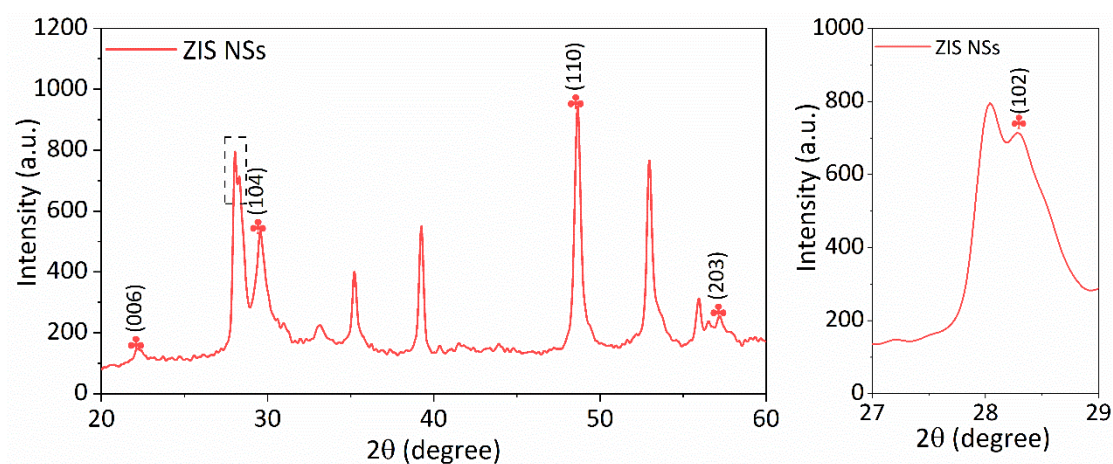


Figure S2. XRD patterns of ZIS (HC).

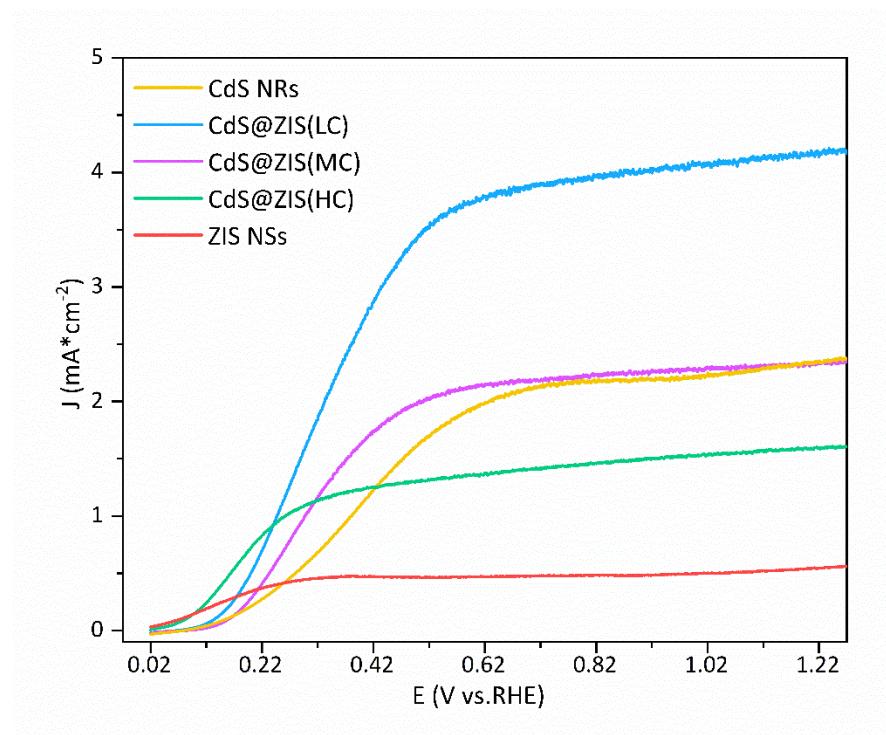


Figure S3. Photocurrent density versus potential curves of CdS NRs, ZIS NSs and CdS@ZIS with varied concentration of ZIS precursor.

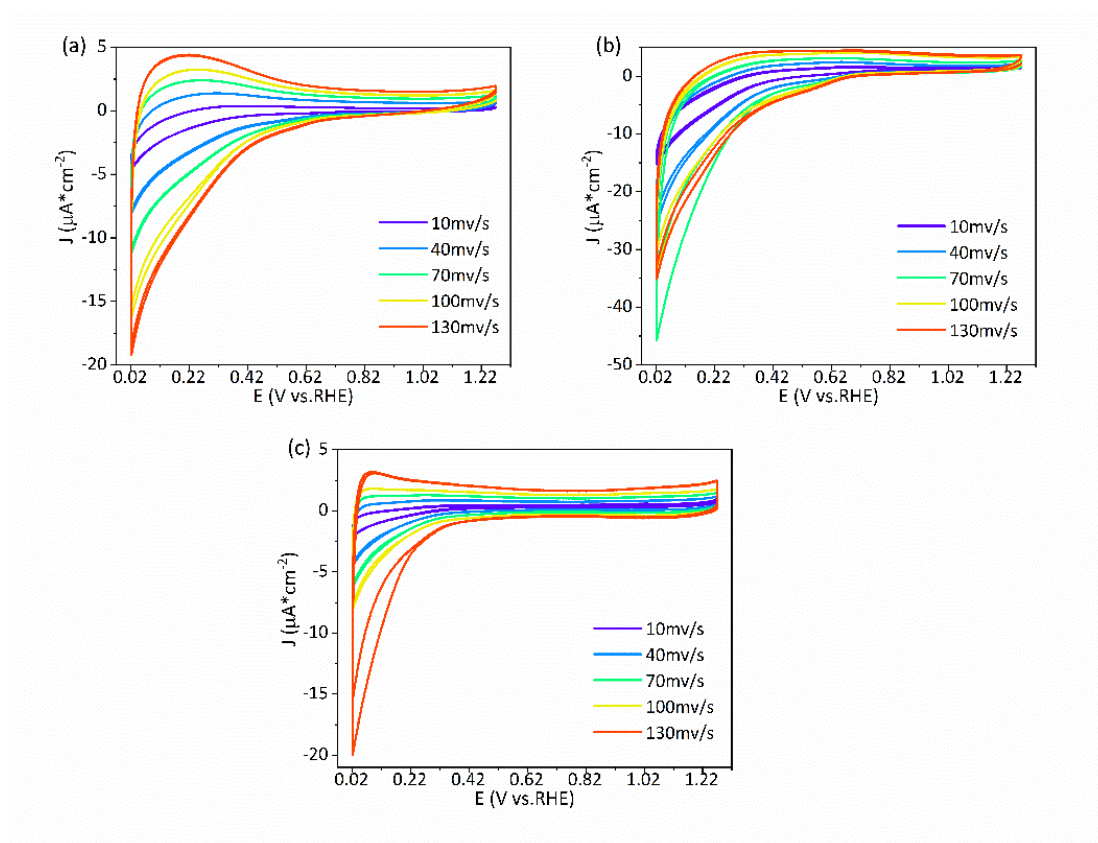


Figure S4. Cyclic voltammograms of (a) CdS NRs, (b) ZIS NSs and (c) CdS@ZIS(LC) at various scan rates from 10 to 130 mV/s.

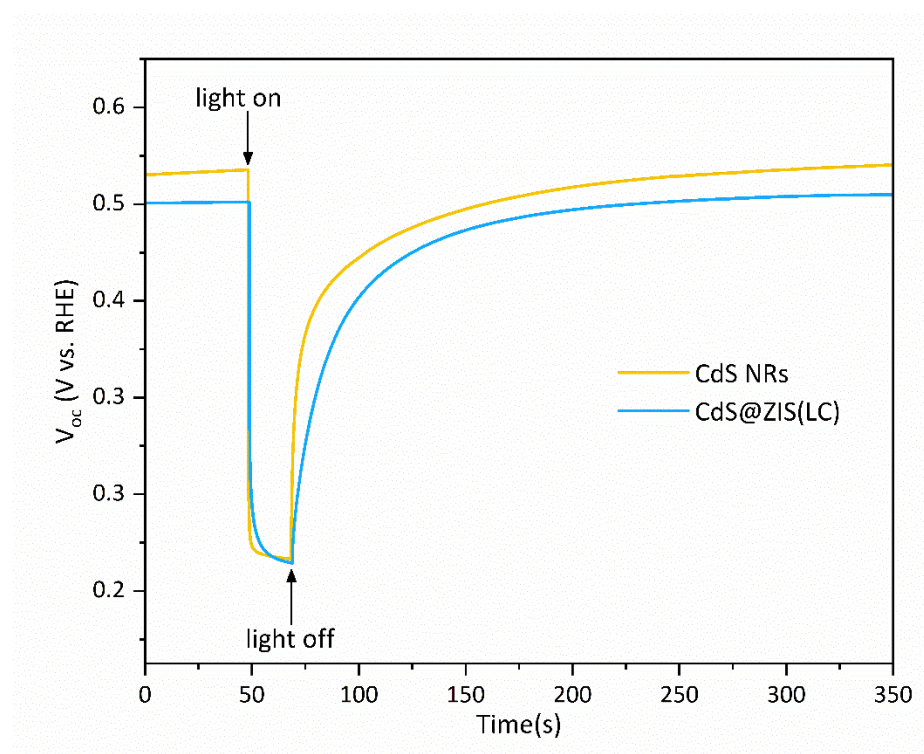


Figure S5. Transient open circuit potential plots under simulated solar light-switching.